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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	HDMI-CEC, I ² C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, I²S, POR, PWM, WDT
Number of I/O	25
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 13x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f051k4t6tr

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can be used either as a watchdog to reset the device when a problem occurs, or as a free running timer for application timeout management. It is hardware or software configurable through the option bytes. The counter can be frozen in debug mode.

3.14.5 System window watchdog (WWDG)

The system window watchdog is based on a 7-bit downcounter that can be set as free running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the APB clock (PCLK). It has an early warning interrupt capability and the counter can be frozen in debug mode.

3.14.6 SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard down counter. It features:

- a 24-bit down counter
- autoreload capability
- maskable system interrupt generation when the counter reaches 0
- programmable clock source (HCLK or HCLK/8)

3.15 Real-time clock (RTC) and backup registers

The RTC and the five backup registers are supplied through a switch that takes power either on V_{DD} supply when present or through the V_{BAT} pin. The backup registers are five 32-bit registers used to store 20 bytes of user application data when V_{DD} power is not present. They are not reset by a system or power reset, or at wake up from Standby mode.

The RTC is an independent BCD timer/counter. Its main features are the following:

- calendar with subseconds, seconds, minutes, hours (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format
- automatic correction for 28, 29 (leap year), 30, and 31 day of the month
- programmable alarm with wake up from Stop and Standby mode capability
- on-the-fly correction from 1 to 32767 RTC clock pulses. This can be used to synchronize the RTC with a master clock
- digital calibration circuit with 1 ppm resolution, to compensate for quartz crystal inaccuracy
- two anti-tamper detection pins with programmable filter. The MCU can be woken up from Stop and Standby modes on tamper event detection
- timestamp feature which can be used to save the calendar content. This function can be triggered by an event on the timestamp pin, or by a tamper event. The MCU can be woken up from Stop and Standby modes on timestamp event detection
- reference clock detection: a more precise second source clock (50 or 60 Hz) can be used to enhance the calendar precision

Table 12. Legend/abbreviations used in the pinout table

Na	me	Abbreviation	Definition					
Pin n	ame		specified in brackets below the pin name, the pin function during and ame as the actual pin name					
		S	Supply pin					
Pin	type	I	Input-only pin					
		I/O	Input / output pin					
		FT	5 V-tolerant I/O					
		FTf	FTf 5 V-tolerant I/O, FM+ capable					
I/O str	ueture	TTa	3.3 V-tolerant I/O directly connected to ADC					
1/0 811	ucture	TC	TC Standard 3.3 V I/O					
		В	Dedicated BOOT0 pin					
		RST	Bidirectional reset pin with embedded weak pull-up resistor					
No	tes	Unless otherwise specified by a note, all I/Os are set as floating inputs during and after reset.						
Pin	Alternate functions	Functions selected through GPIOx_AFR registers						
functions	Additional functions	Functions directly	selected/enabled through peripheral registers					

Table 13. Pin definitions

	P	in nu	umbe	er						Pin functions	
LQFP64	UFBGA64	LQFP48/UFQFPN48	WLCSP36	LQFP32	UFQFPN32	Pin name (function upon reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
1	B2	1	-	-	-	VBAT	S	-	-	Backup po	wer supply
2	A2	2	A6	1	1	PC13	I/O	TC	(1)(2)	-	RTC_TAMP1, RTC_TS, RTC_OUT, WKUP2
3	A1	3	В6	i	-	PC14-OSC32_IN (PC14)	I/O	TC	(1)(2)	-	OSC32_IN
4	B1	4	C6	i	-	PC15-OSC32_OUT (PC15)	I/O	TC	(1)(2)	-	OSC32_OUT
5	C1	5	B5	2	2	PF0-OSC_IN (PF0)	I/O	FT	ı	-	OSC_IN
6	D1	6	C5	3	3	PF1-OSC_OUT (PF1)	I/O	FT	-	-	OSC_OUT



6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

6.1.1 Minimum and maximum values

Unless otherwise specified, the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at $T_A = 25$ °C and $T_A = T_A$ max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean $\pm 3\sigma$).

6.1.2 Typical values

Unless otherwise specified, typical data are based on $T_A = 25$ °C, $V_{DD} = V_{DDA} = 3.3$ V. They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean $\pm 2\sigma$).

6.1.3 Typical curves

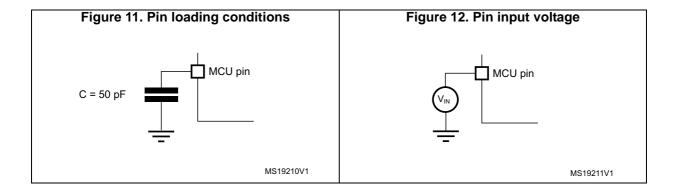
Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in Figure 11.

6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in Figure 12.



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6.1.6 Power supply scheme

 V_{BAT} Backup circuitry (LSE, RTC, Backup registers) 1.65 - 3.6 V Power switch V_{CORE} 2 x V_{DD} Regulator V_{DDIO1} OUT Kernel logic evel shifter Ю 2 x 100 nF (CPU, Digital GP I/Os logic & Memories) +1 x 4.7 µF $2 x V_{SS}$ V_{DDA} 10 nF +1 μF ADC/ Analog: VREF+ DAC (RCs, PLL, ...) VREF-MS34944V1

Figure 13. Power supply scheme

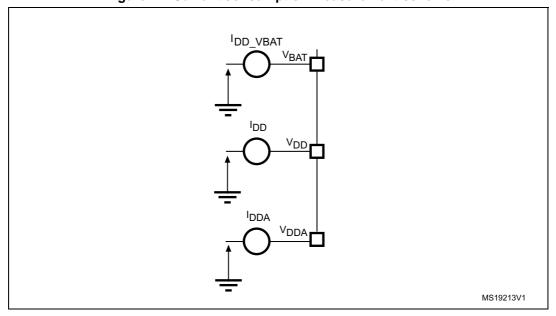
Caution:

Each power supply pair (V_{DD}/V_{SS} , V_{DDA}/V_{SSA} etc.) must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB to ensure the good functionality of the device.

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6.1.7 Current consumption measurement

Figure 14. Current consumption measurement scheme



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6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 17: Voltage characteristics*, *Table 18: Current characteristics* and *Table 19: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 17. Voltage characteristics⁽¹⁾

Symbol	Ratings	Min	Max	Unit	
V _{DD} -V _{SS}	External main supply voltage	- 0.3	4.0	V	
V _{DDA} -V _{SS}	External analog supply voltage	- 0.3	4.0	V	
V _{DD} -V _{DDA}	Allowed voltage difference for $V_{DD} > V_{DDA}$	-	0.4	V	
V _{BAT} -V _{SS}	External backup supply voltage	- 0.3	4.0	٧	
	Input voltage on FT and FTf pins	V _{SS} - 0.3	$V_{\rm DDIOx} + 4.0^{(3)}$	V	
V _{IN} ⁽²⁾	Input voltage on TTa pins	V _{SS} - 0.3	4.0	٧	
VIN.	воото	0	9.0	V	
	Input voltage on any other pin	V _{SS} - 0.3	4.0	V	
ΔV _{DDx}	Variations between different V _{DD} power pins	-	50	mV	
V _{SSx} - V _{SS}	Variations between all the different ground pins	-	50	mV	
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	see Section 6.3.12: Electrical sensitivity characteristics			

All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.

V_{IN} maximum must always be respected. Refer to *Table 18: Current characteristics* for the maximum allowed injected current values.

Valid only if the internal pull-up/pull-down resistors are disabled. If internal pull-up or pull-down resistor is enabled, the maximum limit is 4 V.

Table 25. Typical and maximum current consumption from V_{DD} at 3.6 V (continued)

				All peripherals enabled								
Symbol	Parameter	Conditions	f _{HCLK}	Tun	M	lax @ T	A ⁽¹⁾	Тур	N	lax @ T,	A ⁽¹⁾	Unit
				Тур	25 °C	85 °C	105 °C	iyp	25 °C	85 °C	105 °C	
		HSE	48 MHz	14.0	15.3 ⁽²⁾	15.3	16.0 ⁽²⁾	2.8	3.0 ⁽²⁾	3.0	3.2 ⁽²⁾	
	Cupply	bypass,	32 MHz	9.5	10.2	10.2	10.7	2.0	2.1	2.1	2.3	
		PLL on	24 MHz	7.3	7.8	7.8	8.3	1.5	1.7	1.7	1.9	
		I LL UII	8 MHz	2.6	2.9	2.9	3.0	0.6	8.0	8.0	0.8	
I _{DD}	current in Sleep		1 MHz	0.4	0.6	0.6	0.6	0.2	0.4	0.4	0.4	mA
	mode		48 MHz	14.0	15.3	15.3	16.0	3.8	4.0	4.1	4.2	
		HSI clock, PLL on	32 MHz	9.5	10.2	10.2	10.7	2.6	2.7	2.8	2.8	
			24 MHz	7.3	7.8	7.8	8.3	2.0	2.1	2.1	2.1	
		HSI clock, PLL off	8 MHz	2.6	2.9	2.9	3.0	0.6	0.8	0.8	0.8	

^{1.} Data based on characterization results, not tested in production unless otherwise specified.

Table 26. Typical and maximum current consumption from the V_{DDA} supply

		Conditions		V _{DDA} = 2.4 V					V _{DDA} = 3.6 V			
Symbol	Parameter		f _{HCLK}	Tun	М	ах @ Т _А	(2)	Tun	Max @ T _A ⁽²⁾			Unit
				Тур	25 °C	85 °C	105 °C	Тур	25 °C	85 °C	105 °C	
		HSE	48 MHz	150	170 ⁽³⁾	178	182 ⁽³⁾	164	183 ⁽³⁾	195	198 ⁽³⁾	
	Cummbu	bypass,	32 MHz	104	121	126	128	113	129	135	138	
	Supply current in		24 MHz	82	96	100	103	88	102	106	108	
	Run or Sleep	HSE	8 MHz	2.0	2.7	3.1	3.3	3.5	3.8	4.1	4.4	
I _{DDA}	mode,	bypass, PLL off	1 MHz	2.0	2.7	3.1	3.3	3.5	3.8	4.1	4.4	μΑ
	executing		48 MHz	220	240	248	252	244	263	275	278	
	from Flash memory or	HSI clock, PLL on	32 MHz	174	191	196	198	193	209	215	218	
	RAM		24 MHz	152	167	173	174	168	183	190	192	
		HSI clock, PLL off	8 MHz	72	79	82	83	83.5	91	94	95	

Current consumption from the V_{DDA} supply is independent of whether the digital peripherals are enabled or disabled, being in Run or Sleep mode or executing from Flash memory or RAM. Furthermore, when the PLL is off, I_{DDA} is independent of clock frequencies.



^{2.} Data based on characterization results and tested in production (using one common test limit for sum of I_{DD} and I_{DDA}).

^{2.} Data based on characterization results, not tested in production unless otherwise specified.

^{3.} Data based on characterization results and tested in production (using one common test limit for sum of I_{DD} and I_{DDA}).

Table 27. Typical and maximum current consumption in Stop and Standby modes

Sum	Para-				Тур	@V _{DD} (V _{DD} = V	' _{DDA})						
Sym- bol			Conditions		2.4 V	2.7 V	3.0 V	3.3 V	3.6 V	T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	Unit	
	Supply current	mo	Regulator in run mode, all oscillators OFF		15.1	15.3	15.5	15.7	16	(2)		(2)		
I _{DD}	in Stop mode	pov	gulator in low- wer mode, all sillators OFF	3.2	3.3	3.4	3.5	3.7	4	(2)		(2)		
	Supply current	LSI ON	ON and IWDG	0.8	1.0	1.1	1.2	1.4	1.5	-	-	-		
	in Standby mode	LSI OF	OFF and IWDG F	0.7	0.8	0.9	1.0	1.1	1.3	2 ⁽²⁾	2.5	3 ⁽²⁾		
	Supply current	NO	Regulator in run mode, all oscillators OFF	1.9	2	2.2	2.3	2.5	2.6	3.5 ⁽²⁾	3.5	4.5 ⁽²⁾		
	in Stop mode	monitoring (Regulator in low- power mode, all oscillators OFF	1.9	2	2.2	2.3	2.5	2.6	3.5 ⁽²⁾	3.5	4.5 ⁽²⁾	μA	
	Supply current	V _{DDA} m	LSI ON and IWDG ON	2.3	2.5	2.7	2.9	3.1	3.3	_	-	-		
	in Standby mode	Standby		LSI OFF and IWDG OFF	1.8	1.9	2	2.2	2.3	2.5	3.5 ⁽²⁾	3.5	4.5 ⁽²⁾	
I _{DDA}	Supply current in Stop mode)FF	Regulator in run mode, all oscillators OFF	1.1	1.2	1.2	1.2	1.3	1.4	-	-	-	
			Regulator in low- power mode, all oscillators OFF	1.1	1.2	1.2	1.2	1.3	1.4	-	-	-		
	Supply current	V _{DDA} mc	LSI ON and IWDG ON	1.5	1.6	1.7	1.8	1.9	2.0	-	i	-		
	in Standby mode	Λ	LSI OFF and IWDG OFF	1	1.0	1.1	1.1	1.2	1.2	-	-	-		

^{1.} Data based on characterization results, not tested in production unless otherwise specified.

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^{2.} Data based on characterization results and tested in production (using one common test limit for sum of I_{DD} and I_{DDA}).

Symbol Unit **Parameter Conditions** Min Тур Max TC, FT and FTf I/O TTa in digital mode ± 0.1 $V_{SS} \le V_{IN} \le V_{DDIOx}$ TTa in digital mode 1 Input leakage $V_{\text{DDIO}X} \le V_{\text{IN}} \le V_{\text{DDA}}$ I_{lkg} μΑ current(2) TTa in analog mode ± 0.2 $V_{SS} \le V_{IN} \le V_{DDA}$ FT and FTf I/O 10 $V_{DDIOx} \le V_{IN} \le 5 V$ Weak pull-up R_{PU} equivalent resistor $V_{IN} = V_{SS}$ 25 40 55 kΩ Weak pull-down $V_{IN} = -V_{DDIOx}$ R_{PD} equivalent 25 40 55 kΩ resistor(3)

Table 48. I/O static characteristics (continued)

I/O pin capacitance

All I/Os are CMOS- and TTL-compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements is shown in *Figure 21* for standard I/Os, and in *Figure 22* for 5 V-tolerant I/Os. The following curves are design simulation results, not tested in production.

5

 C_{IO}

рF

^{1.} Data based on design simulation only. Not tested in production.

The leakage could be higher than the maximum value, if negative current is injected on adjacent pins. Refer to Table 47: I/O current injection susceptibility.

Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This PMOS/NMOS contribution to the series resistance is minimal (~10% order).

Symbol	Parameter	Conditions	Min	Max	Unit
t _{su(SD_MR)}	Data input setup time	Master receiver	6	-	
t _{su(SD_SR)}	Data input setup time	Slave receiver	2	-	
t _{h(SD_MR)} ⁽²⁾	Data input hold time	Master receiver	4	-	
t _{h(SD_SR)} (2)	Data input hold time	Slave receiver	0.5	-	200
t _{v(SD_MT)} ⁽²⁾	Data output valid time	Master transmitter	-	4	ns
t _{v(SD_ST)} ⁽²⁾	Data output valid time	Slave transmitter	-	20	
t _{h(SD_MT)}	Data output hold time	Master transmitter	0	-	
t _{h(SD_ST)}	Data output Hold tillle	Slave transmitter	13	-	

Table 64. I²S characteristics⁽¹⁾ (continued)

- 1. Data based on design simulation and/or characterization results, not tested in production.
- 2. Depends on f_{PCLK} . For example, if f_{PCLK} = 8 MHz, then T_{PCLK} = 1/ f_{PLCLK} = 125 ns.

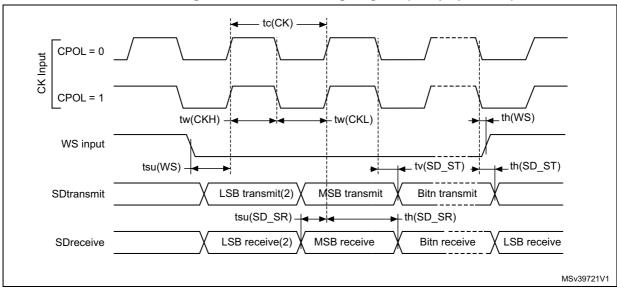


Figure 32. I²S slave timing diagram (Philips protocol)

- 1. Measurement points are done at CMOS levels: $0.3 \times V_{DDIOx}$ and $0.7 \times V_{DDIOx}$
- 2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

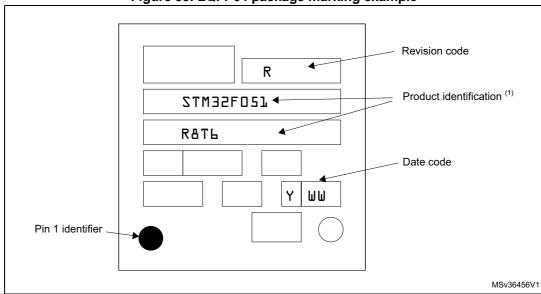


Figure 39. LQFP64 package marking example

1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.



7.3 LQFP48 package information

LQFP48 is a 48-pin, 7 x 7 mm low-profile quad flat package.

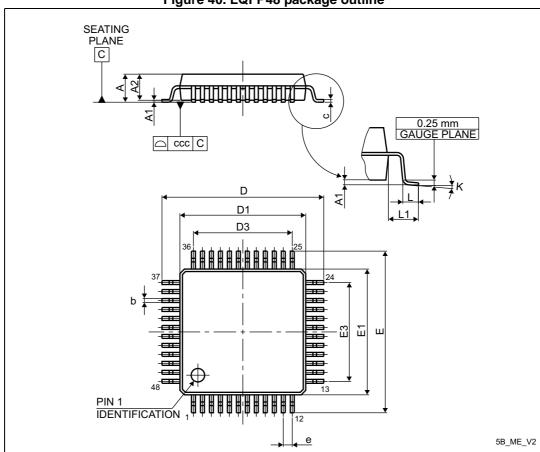


Figure 40. LQFP48 package outline

1. Drawing is not to scale.

Table 68. LQFP48 package mechanical data

0		millimeters			inches ⁽¹⁾	
Symbol	Min	Тур	Max	Min	Тур	Max
Α	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
С	0.090	-	0.200	0.0035	-	0.0079
D	8.800	9.000	9.200	0.3465	0.3543	0.3622
D1	6.800	7.000	7.200	0.2677	0.2756	0.2835
D3	-	5.500	-	-	0.2165	-
E	8.800	9.000	9.200	0.3465	0.3543	0.3622
E1	6.800	7.000	7.200	0.2677	0.2756	0.2835
E3	-	5.500	-	-	0.2165	-
е	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
CCC	-	-	0.080	-	-	0.0031

^{1.} Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 41. Recommended footprint for LQFP48 package 9.70 ai14911d

1. Dimensions are expressed in millimeters.

7.5 WLCSP36 package information

WLCSP36 is a 36-ball, 2.605 x 2.703 mm, 0.4 mm pitch wafer-level chip-scale package.

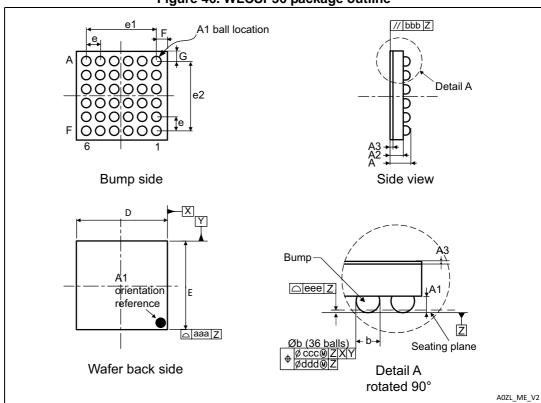


Figure 46. WLCSP36 package outline

1. Drawing is not to scale.

Table 70. WLCSP36 package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Тур	Max	Min	Тур	Max
А	0.525	0.555	0.585	0.0207	0.0219	0.0230
A1	-	0.175	-	-	0.0069	-
A2	-	0.380	-	-	0.0150	-
A3 ⁽²⁾	-	0.025	-	-	0.0010	-
b ⁽³⁾	0.220	0.250	0.280	0.0087	0.0098	0.0110
D	2.570	2.605	2.640	0.1012	0.1026	0.1039
E	2.668	2.703	2.738	0.1050	0.1064	0.1078
е	-	0.400	-	-	0.0157	-
e1	-	2.000	-	-	0.0787	-
e2	-	2.000	-	-	0.0787	-

9 Revision history

Table 76. Document revision history

Date	Revision	Changes
05-Apr-2012	1	Initial release
25-Apr-2012	2	Updated <i>Table:</i> STM32F051xx family device features and peripheral counts for SPI and I ² C in 32-pin package. Corrected Group 3 pin order in <i>Table:</i> Capacitive sensing GPIOs
		available on STM32F051xx devices.
·		Updated the current consumption values in Section: Electrical characteristics.
		Updated Table: HSI14 oscillator characteristics
		Features reorganized and Figure: Block diagram structure changed.
		Added LQFP32 package.
		Updated Section: Cyclic redundancy check calculation unit (CRC).
		Modified the number of priority levels in Section: Nested vectored interrupt controller (NVIC).
		Added note 3. for PB2 and PB8, changed TIM2_CH_ETR into TIM2_CH1_ETR in <i>Table: Pin definitions</i> and <i>Table: Alternate functions selected through GPIOA_AFR registers for port A.</i> Added <i>Table: Alternate functions selected through GPIOB_AFR registers for port B.</i>
23-Jul-2012	3	Updated I _{VDD} , I _{VSS} , and I _{INJ(PIN)} in <i>Table: Current characteristics</i> .
		Updated ACC _{HSI} in <i>Table: HSI oscillator characteristics</i> and <i>Table: HSI14 oscillator characteristics</i> .
		Updated Table: I/O current injection susceptibility.
		Added BOOT0 input low and high level voltage in <i>Table: I/O</i> static characteristics.
		Modified number of pins in V _{OL} and V _{OH} description, and changed condition for V _{OLFM+} in <i>Table: Output voltage characteristics.</i>
		Changed V_{DD} to V_{DDA} in Figure: Typical connection diagram using the ADC.
		Updated Ts_temp in Table: TS characteristics.
		Updated Figure: I/O AC characteristics definition.



Table 76. Document revision history (continued)

Date	Revision	Changes	
		Modified datasheet title.	
		Added packages UFQFPN48 and UFBGA64.	
		Replaced "backup domain with "RTC domain" throughout the document.	
		Changed SRAM value from "4 to 8 Kbyte" to "8 Kbyte"	
		Replaced IWWDG with IWDG in Figure: Block diagram.	
		Added inputs LSI and LSE to the multiplexer in Figure: Clock tree.	
		Added feature "Reference clock detection" in Section: Real-time clock (RTC) and backup registers.	
		Modified junction temperature in <i>Table: Thermal characteristics</i> .	
		Renamed Table: Internal voltage reference calibration values.	
		Replaced V_{DD} with V_{DDA} and V_{RERINT} with ΔV_{REFINT} in <i>Table: Embedded internal reference voltage.</i>	
		Rephrased introduction of Section: Touch sensing controller (TSC).	
13-Jan-2014	4	Rephrased Section: Voltage regulator.	
		Added sentence "If this is used when the voltage regulator is put in low power mode" under "Stop mode" in Section: Low-power modes.	
		Removed sentence "The internal voltage reference is also connected to ADC_IN17 input channel of the ADC." in Section: Comparators (COMP).	
		Removed feature "Periodic wakeup from Stop/Standby" in Section: Real-time clock (RTC) and backup registers.	
		Replaced I _{DD} with I _{DDA} in <i>Table: HSI oscillator characteristics, Table: HSI14 oscillator characteristics</i> and <i>Table: LSI oscillator characteristics</i> .	
		Moved section "Wakeup time from low-power mode" to Section 6.3.6 and rephrased the section.	
		Added lines D2 and E2 in <i>Table: UFQFPN48 – 7 x 7 mm, 0.5 mm pitch, package mechanical data.</i>	
		Added "The peripheral clock used is 48 MHz." in Section <i>On-chip peripheral current consumption.</i>	



Table 76. Document revision history (continued)

Date	Revision	Changes		
Date	Kevision			
28-Aug-2015	5	Updated the following: DAC and power management feature descriptions in Features Table 2: STM32F051xx family device features and peripheral count Section 3.5.1: Power supply schemes Figure 13: Power supply scheme Table 17: Voltage characteristics Table 20: General operating conditions: updated the footnote for V _{IN} parameter Table 28: Typical and maximum current consumption from the V _{BAT} supply Table 52: ADC characteristics Table 33: High-speed external user clock characteristics: replaced V _{DD} with V _{DDIOX} Table 34: Low-speed external user clock characteristics: replaced V _{DD} with V _{DDIOX} Table 37: HSI oscillator characteristics and Figure 19: HSI oscillator accuracy characterization results for soldered parts Table 38: HSI14 oscillator characteristics: changed the min value for ACC _{HSI14} Table 41: Flash memory characteristics: changed the values for t _{ME} and I _{DD} in write mode Table 43: EMS characteristics: changed the value of V _{EFTB} Table 45: ESD absolute maximum ratings Figure 10: STM32F051x8 memory map Figure 21: TC and TTa I/O input characteristics Figure 22: Five volt tolerant (FT and FTf) I/O input characteristics Figure 23: I/O AC characteristics definition tstart definition in Table 24: Embedded internal reference voltage tstart definition in Table 24: Embedded internal reference voltage tstart definition in Table 52: ADC characteristics Table 56: Comparator characteristics: changed the description and values for V _{SC} , V _{DDA} and V _{REFINT} scaler startup time from power down Table 57: TS characteristics: changed the min value for T _{S-vbat} and the typical value for R parameters Section 6.3.22: Communication interfaces: updated the description and features in the subsection I ² C interface characteristics: Table 64: FS characteristics: updated the min values for data input hold time (master and slave receiver)		

